

# Hui Yang

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/3490510/publications.pdf>

Version: 2024-02-01

5  
papers

48  
citations

1937685

4  
h-index

2053705

5  
g-index

5  
all docs

5  
docs citations

5  
times ranked

36  
citing authors

#	ARTICLE	IF	CITATIONS
1	Annealing temperature effects on the structural and electrical properties of N-doped In-Zn-Sn-O thin film transistors. <i>Journal of Alloys and Compounds</i> , 2019, 801, 33-39.	5.5	13
2	Annealing atmosphere-dependent electrical characteristics and bias stability of N-doped InZnSnO thin film transistors. <i>Materials Science in Semiconductor Processing</i> , 2020, 113, 105040.	4.0	12
3	Preparation and electrical characteristics of N-doped In-Zn-Sn-O thin film transistors by radio frequency magnetron sputtering. <i>Journal of Alloys and Compounds</i> , 2018, 750, 1003-1006.	5.5	11
4	Enhancement-mode thin film transistor using amorphous phosphorus-doped Indium-Zinc-Tin-Oxide channel layer. <i>Materials Science in Semiconductor Processing</i> , 2022, 137, 106228.	4.0	7
5	Influence of oxygen flow during sputtering process on the electrical properties of Ga-doped InZnSnO thin film transistor. <i>Semiconductor Science and Technology</i> , 2021, 36, 045006.	2.0	5